1. General description

PNP high power bipolar transistor in a power DPAK, TO-252 (SOT428C) Surface-Mounted Device (SMD) plastic package.

NPN complement: MJD44H11

2. Features and benefits

- · High thermal power dissipation capability
- · High energy efficiency due to less heat generation
- · Electrically similar to popular MJD45H series
- Low collector emitter saturation voltage
- Fast switching speeds

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- · Constant current drive backlighting application
- Motor drive
- Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-80	V
I _C	collector current		-	-	-8	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-16	Α
h _{FE}	DC current gain	$V_{CE} = -1 \text{ V; } I_{C} = -2 \text{ A; } T_{amb} = 25 \text{ °C}$	60	-	-	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	mb	E
2	С	collector		в -{м
3	Е	emitter		C; mb
mb	С	mounting base; connected to collector	DPAK (SOT428C)	aaa-029523

6. Ordering information

Table 3. Ordering information

- table of ortioning morning m						
Type number	Package					
	Name	Description	Version			
MJD45H11	DPAK	Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428C			

7. Marking

Table 4. Marking codes

Type number	Marking code
MJD45H11	MJD45H11

8. Limiting values

Table 5. Limiting values

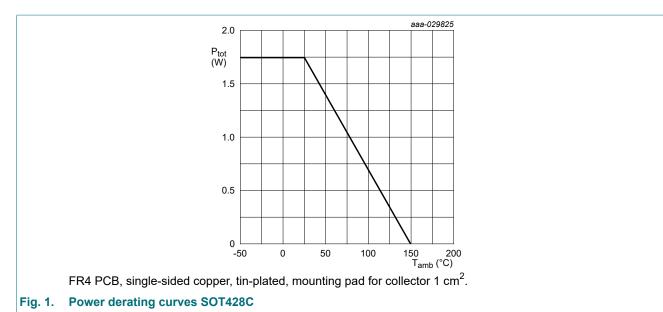
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-80	V
V_{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-8	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-16	А
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C	[1]	-	20	W
		T _{amb} ≤ 25 °C	[2]	-	1.75	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Total power dissipation junction to mounting base.

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 1 cm².

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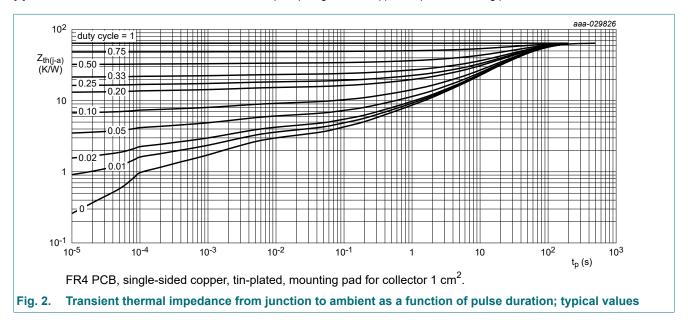


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	in free air		-	-	6.25	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	-	72	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 1 cm².



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CES}	collector-emitter cut-off	V _{CE} = -64 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-1	μΑ
	current	V _{CE} = -64 V; V _{BE} = 0 V; T _j = 150 °C	-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-1	μΑ
h _{FE}	DC current gain	V _{CE} = -1 V; I _C = -2 A; T _{amb} = 25 °C	60	-	-	
		V _{CE} = -1 V; I _C = -4 A; T _{amb} = 25 °C	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -8 A; I_B = -400 mA; T_{amb} = 25 °C	-	-	-1	V
V _{BEsat}	base-emitter saturation voltage	I_C = -8 A; I_B = -800 mA; T_{amb} = 25 °C	-	-	-1.5	V
t _{on}	turn-on time	$I_C = -5 \text{ A}$; $I_{Bon} = -0.5 \text{ A}$; $I_{Boff} = 0.5 \text{ A}$;	-	225	-	ns
t _s	storage time	V _{CC} = -12.5 V; T _{amb} = 25 °C	-	280	-	ns
t _f	fall time		-	100	-	ns
t _{off}	turn-off time		-	380	-	ns
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 ^{\circ}\text{C}$	-	80	-	pF
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -500 mA; f = 100 MHz; T_{amb} = 25 °C	-	80	-	MHz

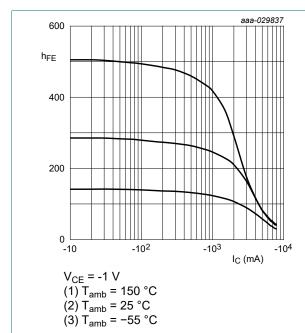


Fig. 3. DC current gain as a function of collector current; typical values

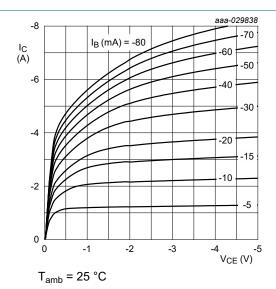
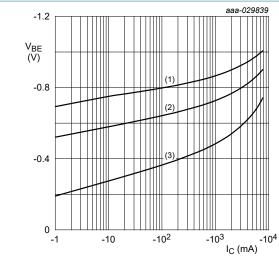


Fig. 4. Collector current as a function of collectoremitter voltage; typical values

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V_{CEsat}

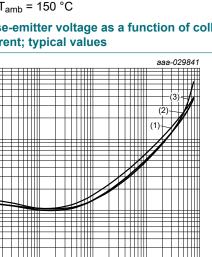
-10⁻¹

-10⁻²

-10⁻³

V_{CE} = -5 V (1) T_{amb} = -55 °C (2) T_{amb} = 25 °C (3) T_{amb} = 150 °C

Fig. 5. Base-emitter voltage as a function of collector current; typical values



-10⁴ I_C (mA)

-10³

 $I_{\rm C}/I_{\rm B}=20$

(1) T_{amb} = 150 °C

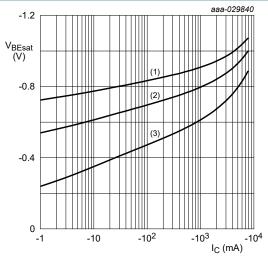
-10

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

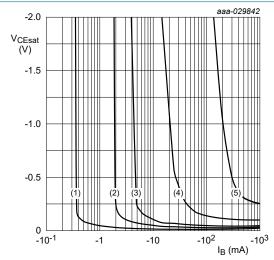
-10²



 $I_{C}/I_{B} = 20$ (1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$

(3) T_{amb} = 150 °C

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values



(1) $I_C = -100 \text{ mA}$

(2) $I_C = -500 \text{ mA}$

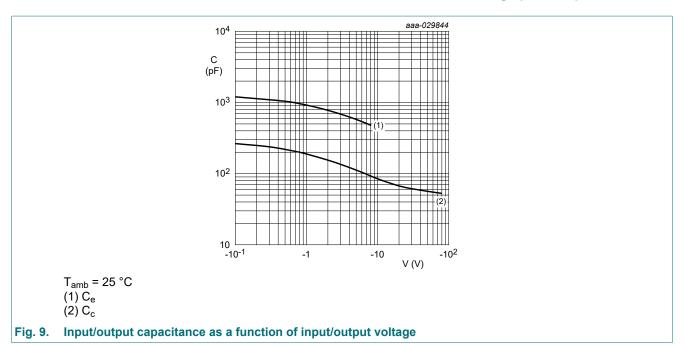
(3) $I_C = -1000 \text{ mA}$

(4) $I_C = -3000 \text{ mA}$

 $(5) I_C = -8000 \text{ mA}$

Fig. 8. Collector-emitter saturation region as a function of base current; typical values

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11. Test information

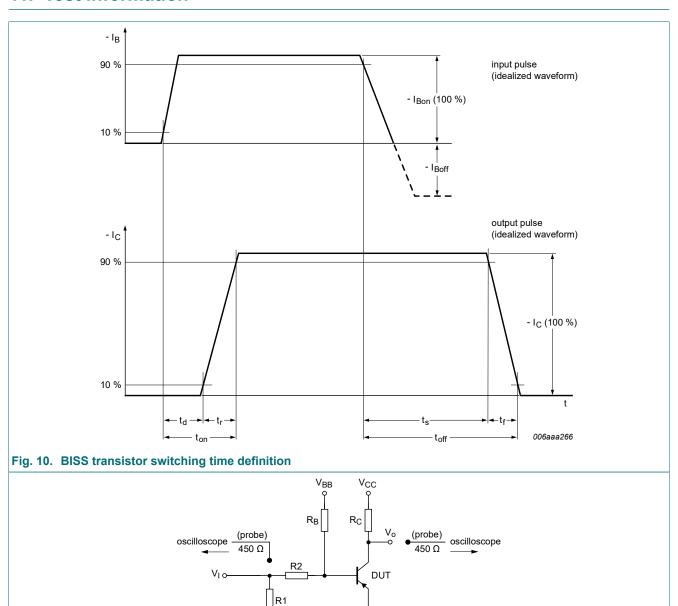


Fig. 11. Test circuit for switching times

mgd624

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12. Package outline

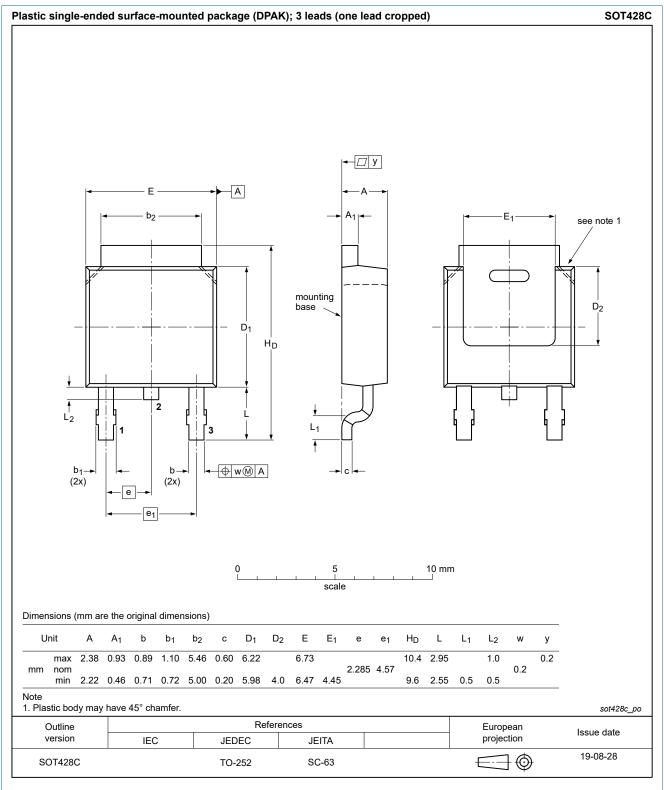
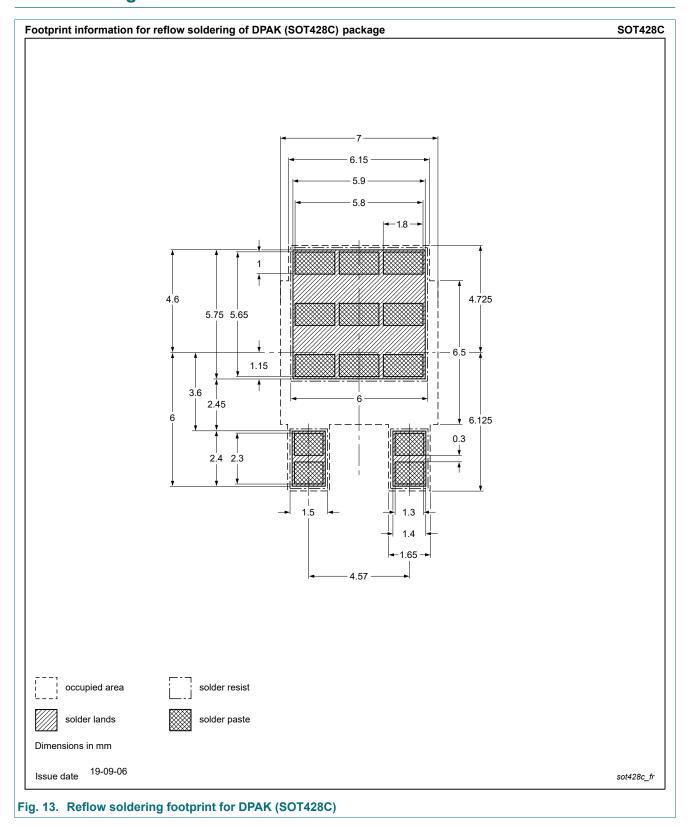


Fig. 12. Package outline DPAK (SOT428C)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
MJD45H11 v.3	20190912	Product data sheet	-	MJD45H11 v.2			
Modifications:	Package outling	Package outline adapted to SOT428C					
MJD45H11 v.2	20190729	Product data sheet	-	MJD45H11 v.1			
MJD45H11 v.1	20190528	Preliminary data sheet	-	-			

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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